NSN 5961-01-155-1352

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View Online at https://aerobasegroup.com/nsn/5961-01-155-1352
Inclosure Material:
Metal
Overall Length:
0.210 inches
Terminal Length:
0.500 inches
Overall Diameter:
0.230 inches
Internal Configuration:
Junction contact
Joint Electronic Device Engineering Council/jedec/case Outline Designation:
To-18
Electrode Internally-electrically Connected To Case:
Anode
Mounting Method:
Terminal
Terminal Circle Diameter:
0.100 inches
Features Provided:
Hermetically sealed case
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
100.0 repetitive peak off-state voltage
Current Rating Per Characteristic:
275.00 milliamperes forward current, total rms nanoamperes
Power Rating Per Characteristic:
100.0 milliwatts small-signal input power, common-collector peak
Maximum Operating Tempurature Per Measurement Point:
150.0 degrees celsius junction
Special Features:
Internal junction configuration arrangement pnpn
Terminal Type And Quantity:
3 uninsulated wire lead
Specification Data:
80131-release6646 professional/industrial association specification
Shelf Life:
N/a
Unit Of Measure:
Demilitarization:

No

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